Alfa-MOS Technology

AFN7110S
40V N-Channel Enhancement Mode MOSFET

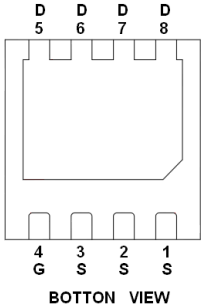
General Description

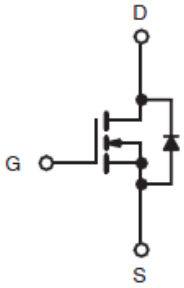
AFN7110S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.
These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

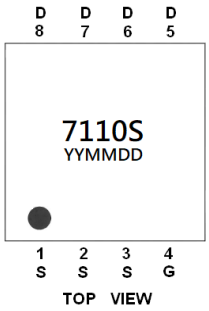
Features

- I_D=20A,$R_{DS(ON)}$=4.5mΩ@V_{GS}=10V
- I_D=15A,$R_{DS(ON)}$=5.4mΩ@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3X3-8L package design

Pin Description (DFN3X3-8L)







Application

- DC-DC Converter
- POL

Pin Define

Pin	Symbol	Description
1~3	S	Source
4	G	Gate
5~8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN7110SFN338RG	7110S	DFN3X3-8L	Tape & Reel	5000 EA

※ YY year code
※ MM month code
※ DD date code
※ AFN7110SFN338RG : 13”Tape & Reel ; Pb- Free ; Halogen –Free

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Absolute Maximum Ratings(T_A=25℃ Unless otherwise noted)

Parameter			Symbol	Typical		Unit
Drain-Source Voltage			V_{DSS}	40		V
Gate –Source Voltage			V_{GSS}	±20		V
Continuous Drain Current(T_J=150℃)	T_C=25℃	T_C=70℃	I_{DSM}	108	86	A
	T_A=25℃	T_A=70℃		32	25	
Pulsed Drain Current (t=100us)			I_{DM}	150		
Continuous Source Current(Diode Conduction)	T_C=25℃		I_S	51		
	T_A=25℃			4.3		
Single Pulse Avalanche Current	L=0.1mH		I_{AS}	30		
			E_{AS}	45		mJ
Power Dissipation	T_C=25℃	T_C=75℃	P_D	56	36	W
	T_A=25℃	T_A=75℃		4.8	3.0	
Operating Junction Temperature			T_J	150		℃
Storage Temperature Range			T_{STG}	-55/150		℃
Thermal Resistance-Junction to Ambient	t ≤ 10 s		$R_{\theta JA}$	26		℃/W
Maximum Junction-to-Case (Drain)	Steady-State		$R_{\theta JA}$	2.2		

Electrical Characteristics(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0		2.5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=32V,V_{GS}=0V			1	uA
		V_{DS}=32V,V_{GS}=0V T_J=85℃			10	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=10V	30			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=20A		3.9	4.5	mΩ
		V_{GS}=4.5V,I_D=15A		4.9	5.4	
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=15A		80		S
Diode Forward Voltage	V_{SD}	I_S=5A,V_{GS}=0V		0.75	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=20V,V_{GS}=4.5V I_D≡10A		18	36	nC
Gate-Source Charge	Q_{gs}			9.5		
Gate-Drain Charge	Q_{gd}			3.0		
Gate Resistance	R_g	f=1MHz		1.7		Ω
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1MHz		2650		pF
Output Capacitance	C_{oss}			860		
Reverse Transfer Capacitance	C_{rss}			80		
Turn-On Time	$t_{d(on)}$	V_{DD}=20V,R_L=1Ω I_D≡10A,V_{GEN}=10V R_G=1Ω		15	30	ns
	t_r			5	10	
Turn-Off Time	$t_{d(off)}$			30	60	
	t_f			5	10	

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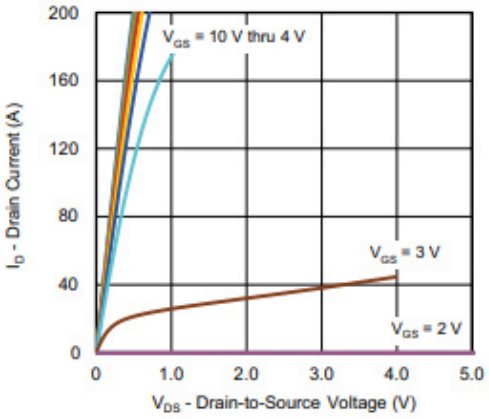
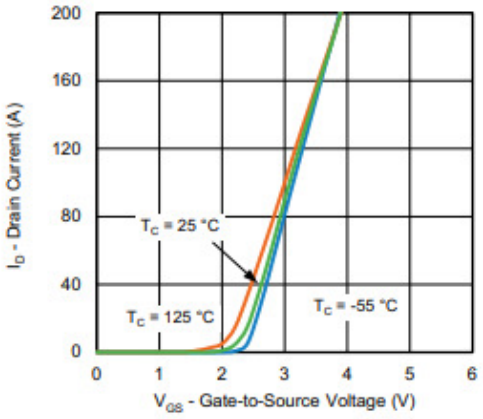
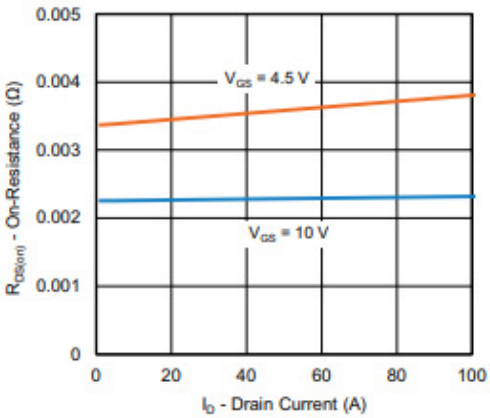
Typical Characteristics



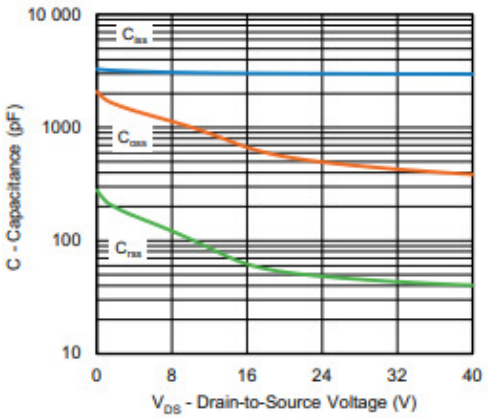
Output Characteristics



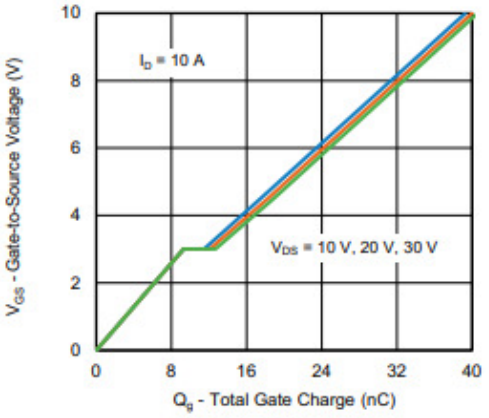
Transfer Characteristics



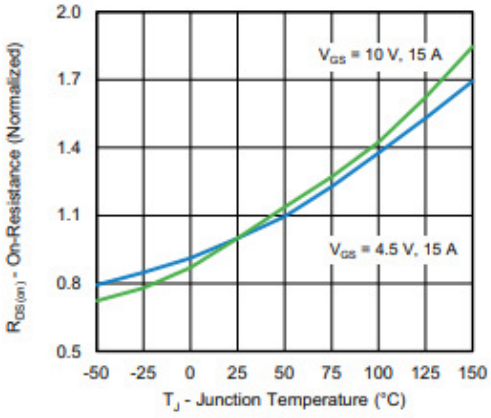
On-Resistance vs. Drain Current



Capacitance

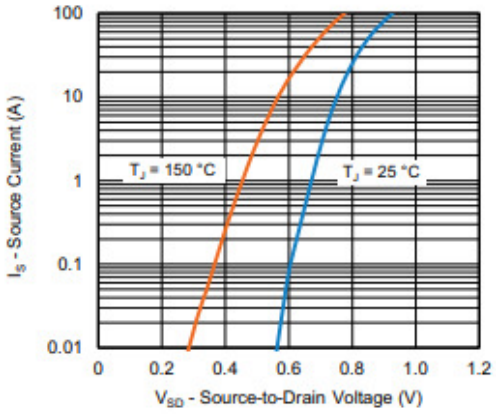


Gate Charge

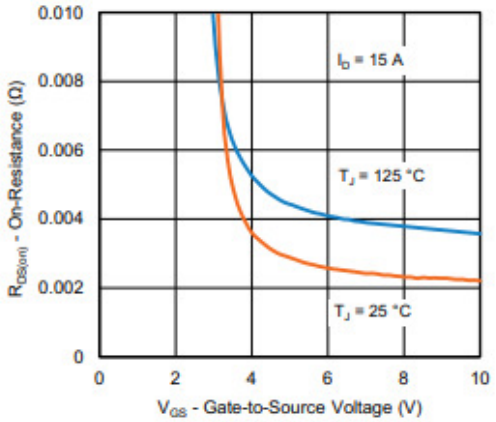


On-Resistance vs. Junction Temperature

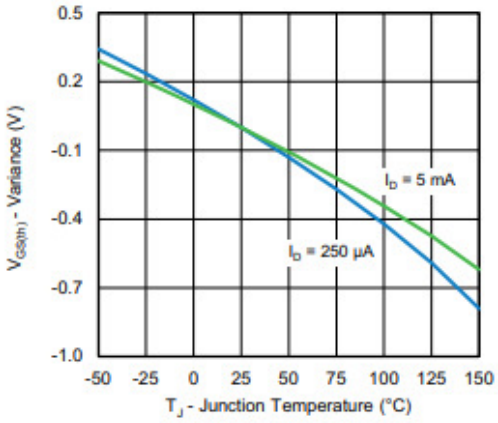
Typical Characteristics



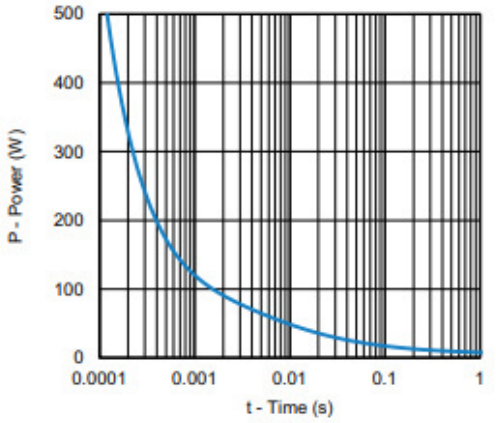
Source-Drain Diode Forward Voltage



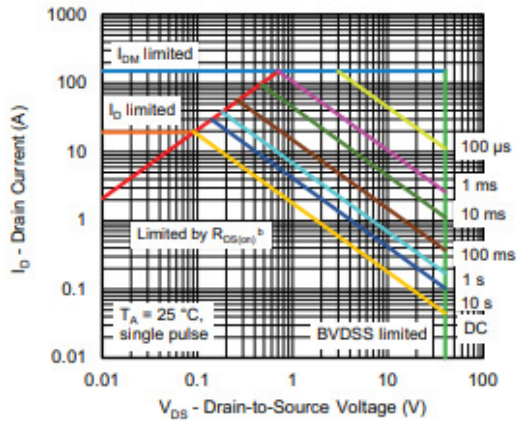
On-Resistance vs. Gate-to-Source Voltage



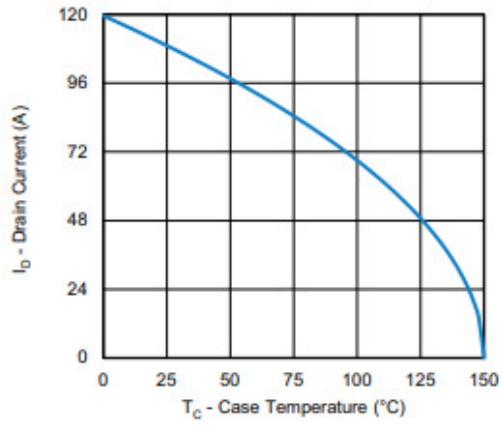
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

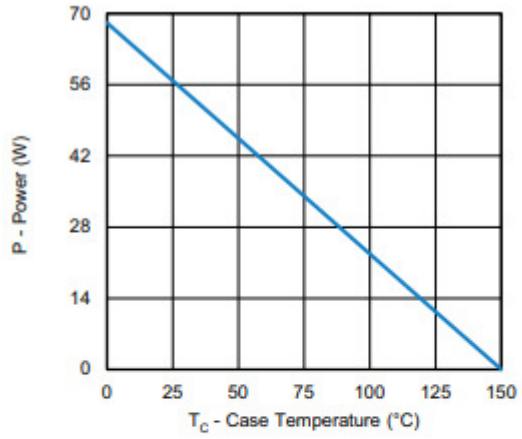


Safe Operating Area

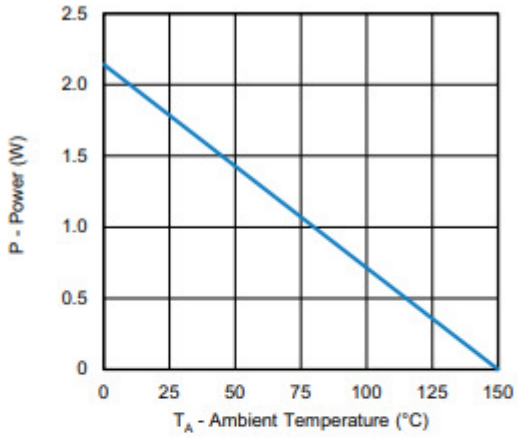


Current Derating [a]

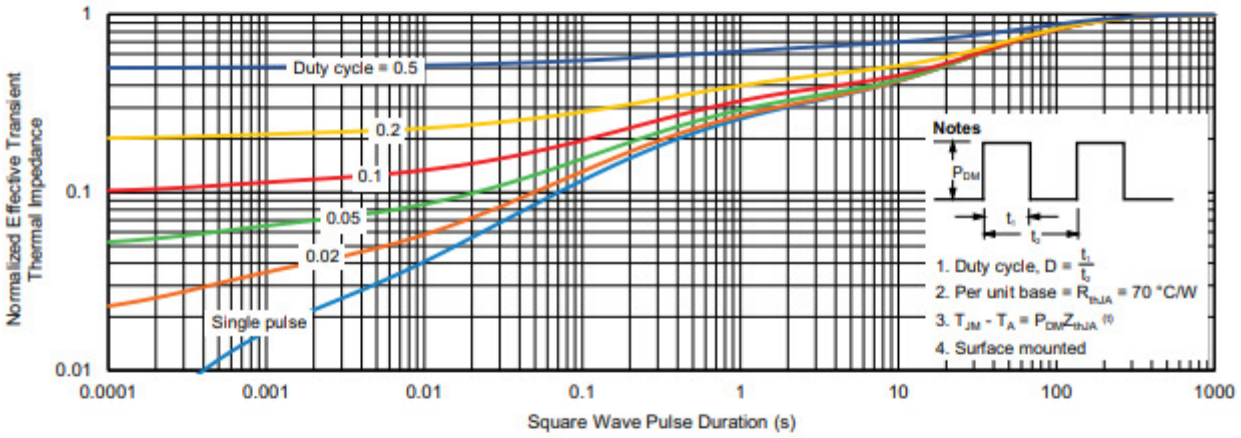
Typical Characteristics



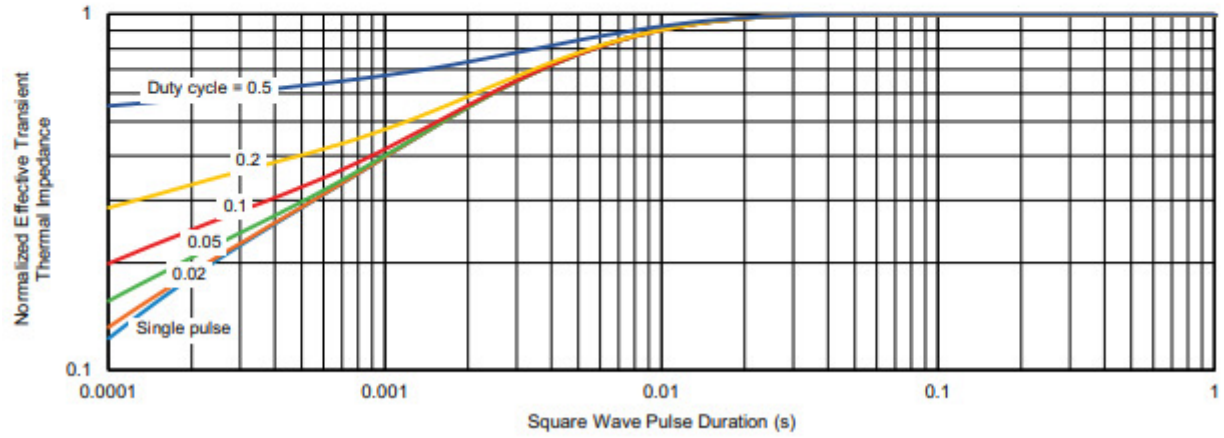
Power, Junction-to-Case



Power, Junction-to-Ambient



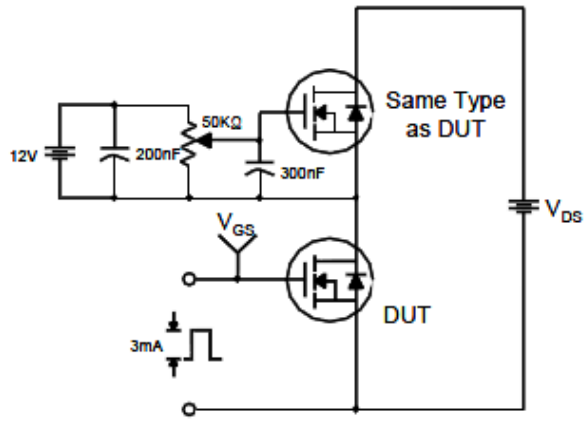
Normalized Thermal Transient Impedance, Junction-to-Ambient

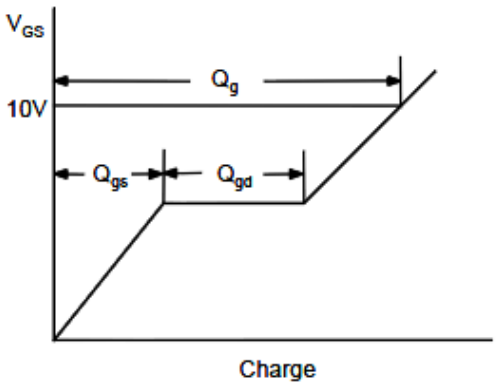


Normalized Thermal Transient Impedance, Junction-to-Case

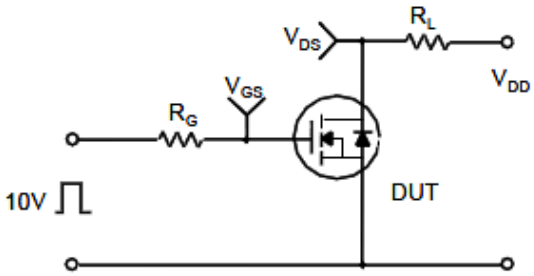
Typical Characteristics

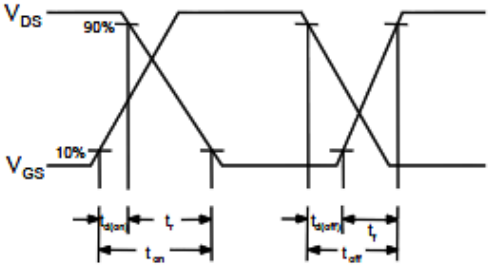
Gate Charge Test Circuit & Waveform



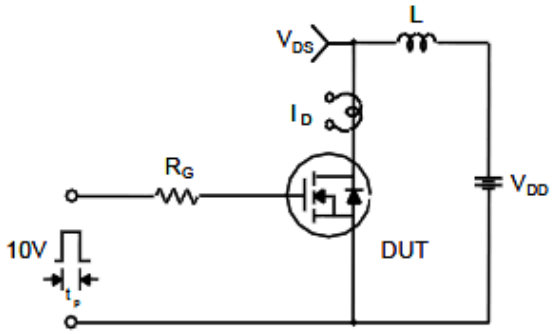


Resistive Switching Test Circuit & Waveforms

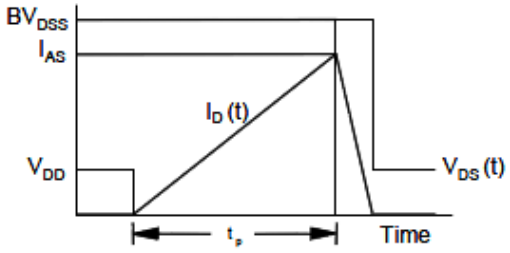




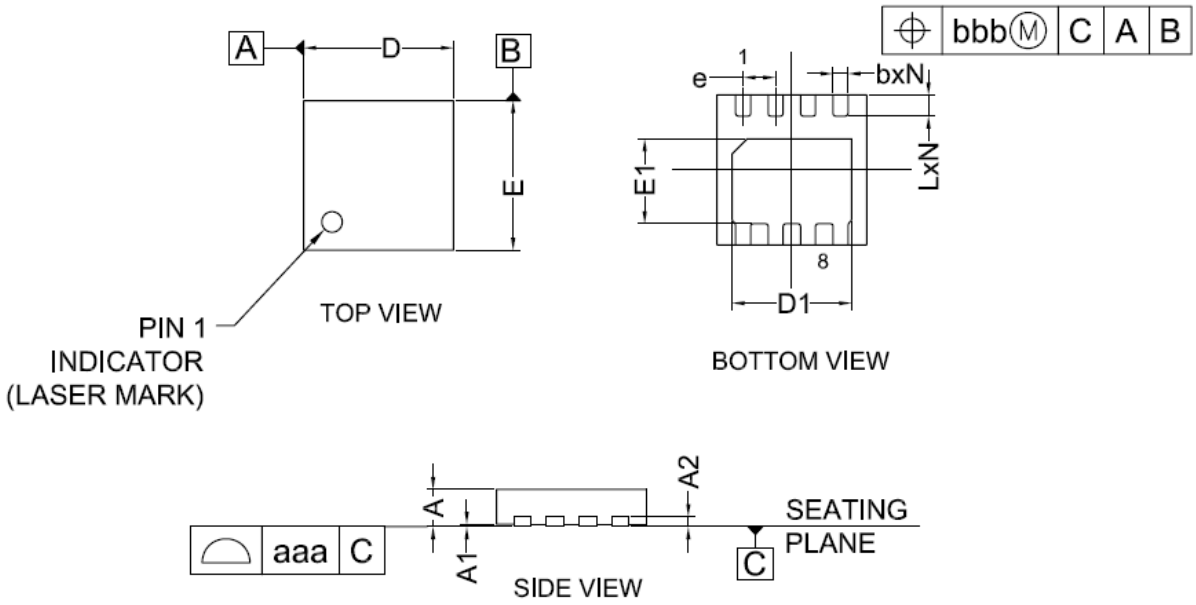
Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Package Information (DFN3X3-8L)



SYMBOL	MIN	TYP	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2		0.203	
b	0.25	0.30	0.35
D	2.90	3.00	3.10
D1	2.35	2.40	2.45
E	2.90	3.00	3.10
E1	1.65	1.70	1.75
e		0.65BSC	
L	0.37	0.42	0.47
N		8	
aaa		0.08	
bbb		0.10	

COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

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2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)
Tel : 886 2) 2651 3928
Fax : 886 2) 2786 8483
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